

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE7190H uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = 71V, I_D = 90A$ $R_{DS(ON)} < 6.8m\Omega @ V_{GS} = 10V$ (Typ:5.9m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!

Schematic diagram

(2) D

(3) s

(1) GO

TO-220H-3L top view

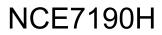
Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| NCE7190H | NCE7190H | TO-220-3L | - | - | - |

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

| Parameter | Symbol | Limit | Unit | |
|--|-----------------------|------------|------|--|
| Drain-Source Voltage | Vds | 71 | V | |
| Gate-Source Voltage | V _{GS} | ±20 | V | |
| Drain Current-Continuous | I _D | 90 | А | |
| Drain Current-Continuous(T _C =100℃) | I _D (100℃) | 63 | A | |
| Pulsed Drain Current | I _{DM} | 320 | A | |
| Maximum Power Dissipation | PD | 170 | W | |
| Derating factor | | 1.13 | W/°C | |
| Single pulse avalanche energy (Note 5) | E _{AS} | 550 | mJ | |
| Operating Junction and Storage Temperature Range | TJ,TSTG | -55 To 175 | °C | |





Thermal Characteristic

| Thermal Resistance, Junction-to-Case (Note 2) | R _{θJc} | 0.88 | °C/W |
|---|------------------|------|------|
|---|------------------|------|------|

Electrical Characteristics (T_c=25 $^{\circ}$ Cunless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|--|-----|-------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250µA | 71 | 74 | _ | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =71V,V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | · | · | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} ,I _D =250µA | 2 | 3 | 4 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =40A | - | 5.9 | 6.8 | mΩ |
| Forward Transconductance | g fs | V _{DS} =10V,I _D =40A | - | 50 | - | S |
| Dynamic Characteristics (Note4) | · | · | | | | |
| Gate resistance | Rg | V _{DS} =0V,V _{GS} =0V,F=1.0MHz | - | 0.63 | - | Ω |
| Input Capacitance | C _{lss} | | - | 4871 | - | PF |
| Output Capacitance | Coss | V _{DS} =15V,V _{GS} =0V, F=1.0MHz | - | 630.6 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | | - | 410.3 | - | PF |
| Switching Characteristics (Note 4) | · | · | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 36.1 | - | nS |
| Turn-on Rise Time | tr | V _{DD} =30V,I _D =30A | - | 54.3 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =10V, R_{GEN} =10 Ω | - | 85.2 | - | nS |
| Turn-Off Fall Time | t _f | | - | 37.3 | - | nS |
| Total Gate Charge | Qg | N/ 40\// 00A | - | 85.7 | - | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} =48V,I _D =30A, V _{GS} =10V | - | 23.2 | - | nC |
| Gate-Drain Charge | Q _{gd} | V _{GS} =10V | - | 31.2 | - | nC |
| Drain-Source Diode Characteristics | · | · | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =20A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | I _S | - | - | - | 90 | А |
| Reverse Recovery Time | t _{rr} | TJ = 25°C, IF =40A | - | 88.3 | _ | nS |
| Reverse Recovery Charge | Qrr | di/dt = 100A/µs ^(Note3) | | 65.9 | - | nC |
| Forward Turn-On Time | t _{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |
| | | | | | | |

Notes:

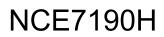
1. Repetitive Rating: Pulse width limited by maximum junction temperature.

- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^\circ \!\! \mathbb{C}$,V_DD=35V,V_G=10V,L=0.5mH,Rg=25\Omega

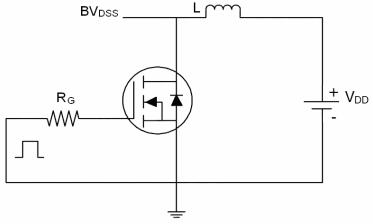


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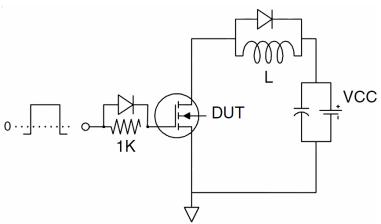
Pb Free Product



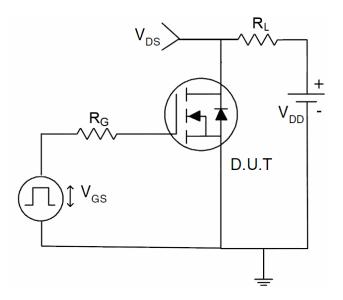
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit

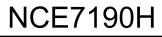


3) Switch Time Test Circuit

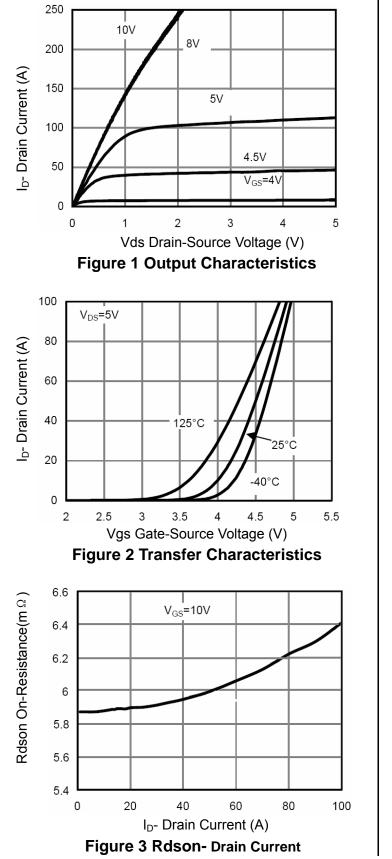


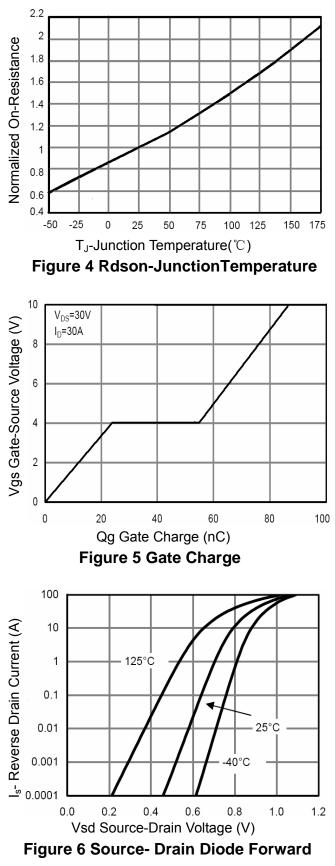






Typical Electrical and Thermal Characteristics (Curves)

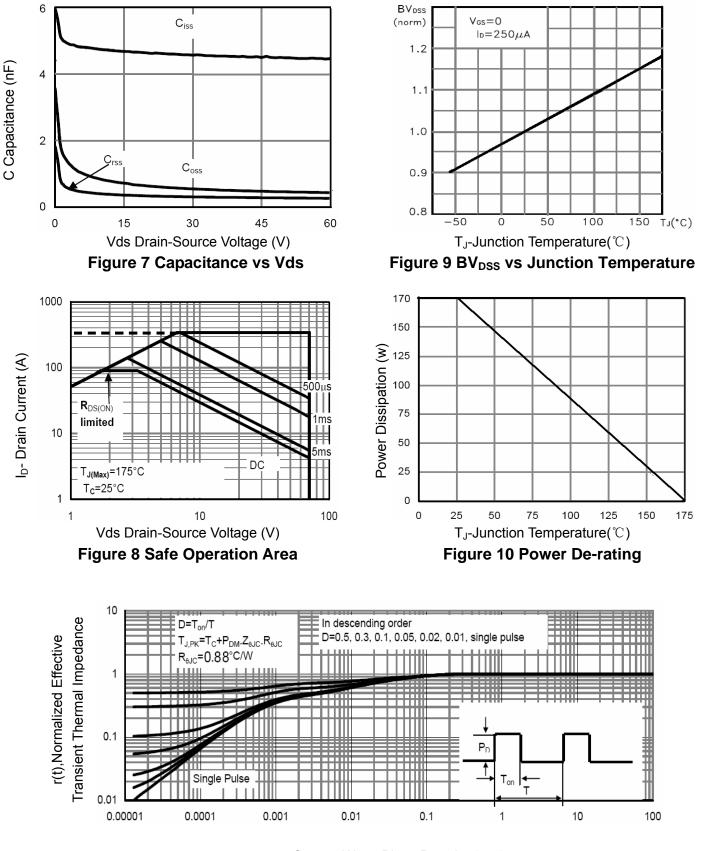


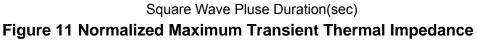






NCE7190H



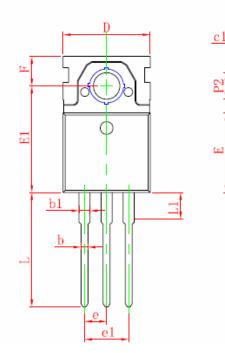


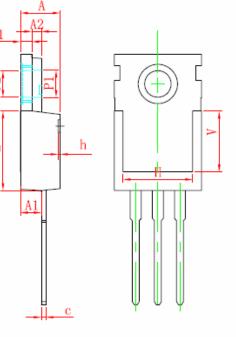




NCE7190H

TO-220H-3L Package Information





| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| Symbol | Min. | Max. | Min. | Max. | |
| A | 4.400 | 4.600 | 0.173 | 0.181 | |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| A2 | 1.000 | 1.200 | 0.039 | 0.047 | |
| b | 0.710 | 0.910 | 0.028 | 0.036 | |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 | |
| с | 0.330 | 0.650 | 0.013 | 0.026 | |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 | |
| D | 9.820 | 10.220 | 0.387 | 0.402 | |
| E | 8.950 | 9.350 | 0.352 | 0.368 | |
| E1 | 12.000 | 12.500 | 0.472 | 0.492 | |
| e | 2.540 | TYP. | 0.100 TYP. | | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 | |
| F | 3.250 | 3.550 | 0.128 | 0.140 | |
| Н | 7.900 | 8.100 | 0.311 | 0.319 | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | |
| L | 12.930 | 13.330 | 0.509 | 0.525 | |
| L1 | 3.450 | 3.850 | 0.136 | 0.152 | |
| P1 | 3.15 | TYP. | 0.124 TYP. | | |
| P2 | 3.05 | TYP. | 0.120 TYP. | | |
| V | 6.900 | REF. | 0.272 REF. | | |







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